

Towards Highly Efficient Thermally Activated Delayed Fluorescence Devices through a Trap-assisted Recombination Mechanism and Reduced Interfacial Excitons Annihilation

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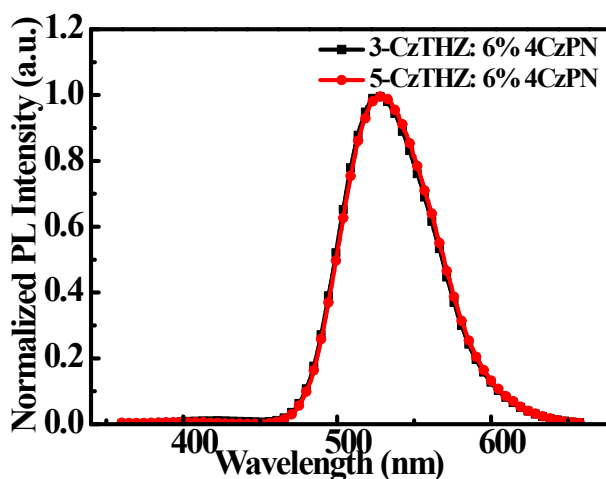


Fig. S1 The PL spectra of doped films for 3-CzTHZ : 6 wt% 4CzPN and 5-CzTHZ : 6 wt% 4CzPN.

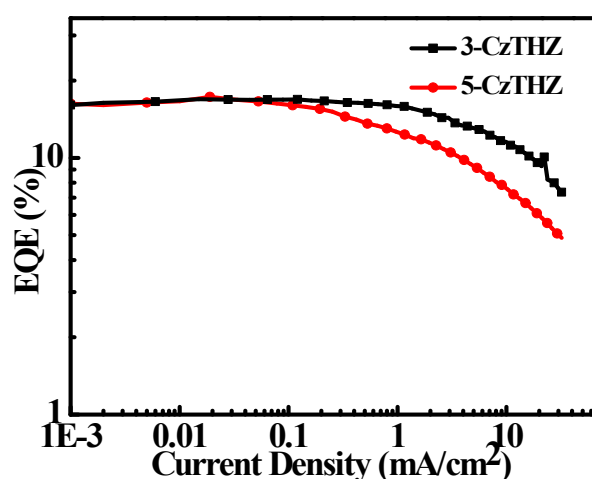


Fig. S2 EQE-current density properties of devices A and B hosted by 3-CzTHZ and 5-CzTHZ, respectively.

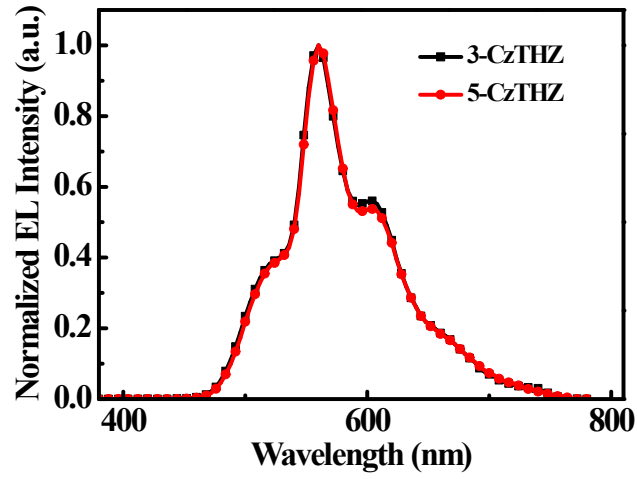


Fig. S3 EL spectra of two devices by inserting an ultrathin $(\text{fbi})_2\text{Ir}(\text{acac})$ sensor layer closed to the ETL side.

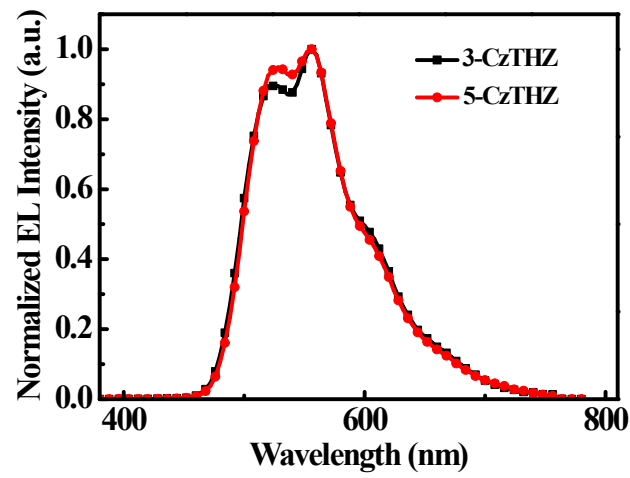


Fig. S4 EL spectra of two devices by inserting an ultrathin $(\text{fbi})_2\text{Ir}(\text{acac})$ sensor layer in the middle of the EML.